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(54) Title: METHODS FOR DAMAGE ETCH AND TEXTURING OF SILICON SINGLE CRYSTAL SUBSTRATES

(57) Abstract: Methods for performing damage etch and texturing of single crystal silicon substrates, particularly for use as solar cells or photovoltaic cells. Damage etch with a TMAH solution followed by texturing using solution of KOH or NaOH mixed with IPA is particularly advantageous. The substitution of some of the IPA with ethylene glycol further improves results. Also disclosed is a process that combines both damage etch and texturing etch into a single step.



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